



Peak pulse voltage ( $T_j=25$ ; non-repetitive, off-state; FIG.7)	$V_{pp}$	4	kV
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## ELECTRICAL CHARACTERISTICS (unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
$I_{GT}$	$V_D=12V R_L=33$	- -	MAX.	10	mA
$V_{GT}$		- -	MAX.	1	V
$V_{GD}$	$V_D=V_{DRM} T_j=125$ $R_L=3.3k$	- -	MIN.	0.2	V
$I_L$	$I_G=1.2I_{GT}$	-	MAX.	25	mA
				30	
$I_H$	$I_T=500mA$		MAX.	15	mA
dV/dt	$V_D=800V$ Gate Open $T_j=125$		MIN.	100	V s
(dI/dt) <sub>c</sub>	(dV/dt) <sub>c</sub> =1.9 $V_j=125$		MIN.	5	A/ms
$t_{on}$	$I_G=20mA I_A=200mA I_R=20mA$ $T_j=25$		TYP.	5	s
$t_{off}$				30	

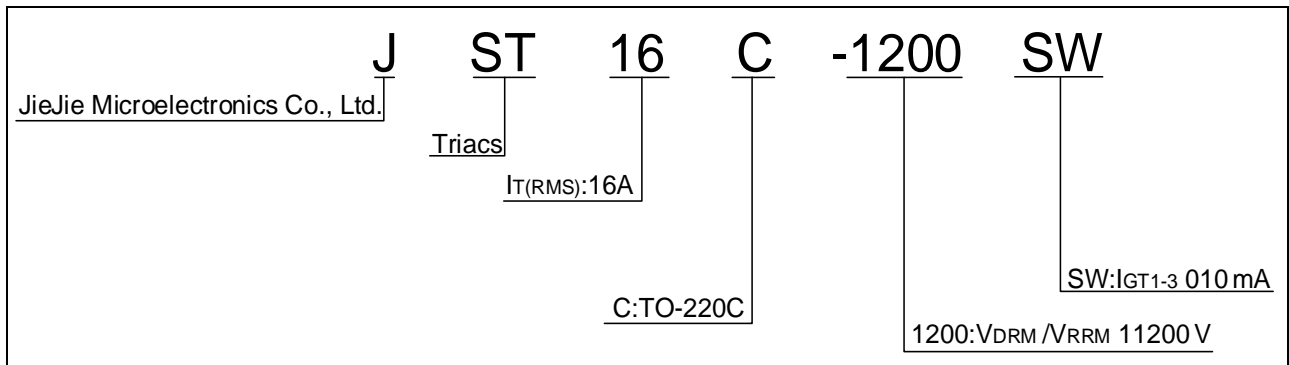
## STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX.)	Unit
$V_{TM}$	$I_{TM}=22.5A t_p=380 \mu s$	$T_j=25$	1.5	V
$V_{TO}$	Threshold voltage	$T_j=125$	0.77	V
$R_D$	Dynamic resistance	$T_j=125$	32	P
$I_{DRM}$	$V_D=V_{DRM} V_R=V_{RRM}$	$T_j=25$	10	A
$I_{RRM}$		$T_j=125$	2	mA

## THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (AC)	1.1	$^{\circ}W$
$R_{th(j-a)}$	junction to ambient (AC)	60	$^{\circ}W$

ORDERING INFORMATION



MARKING

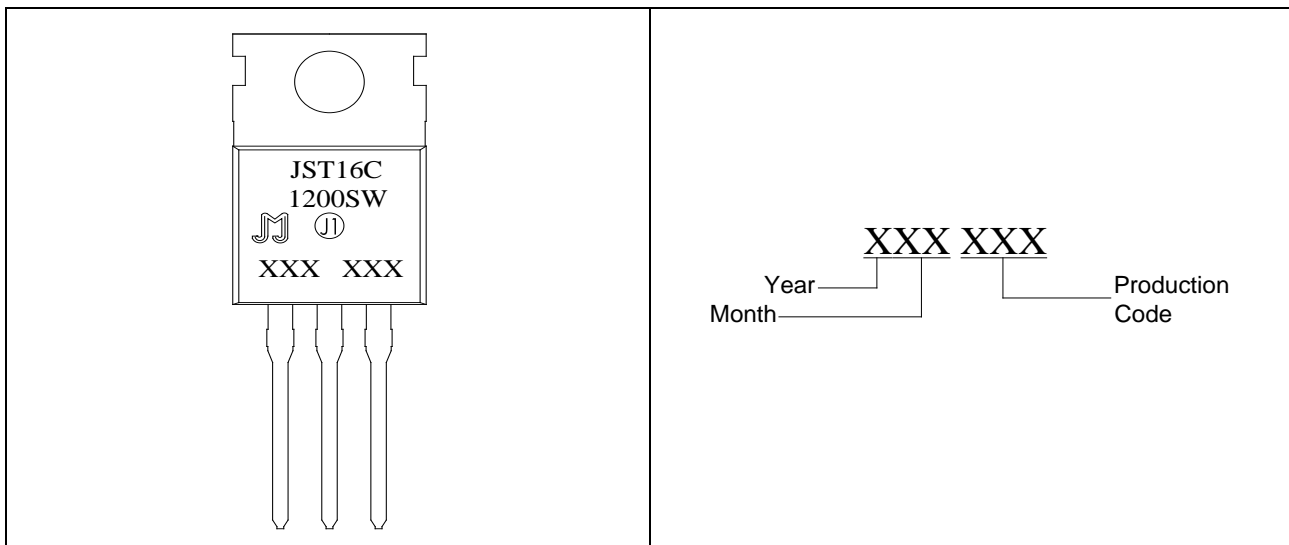


FIG.1: Maximum power dissipation versus RMS on-state current

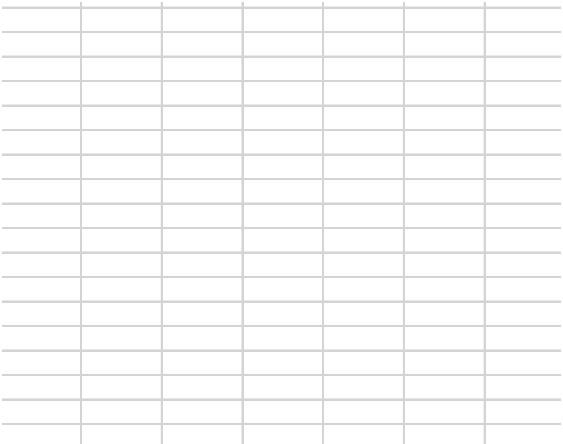
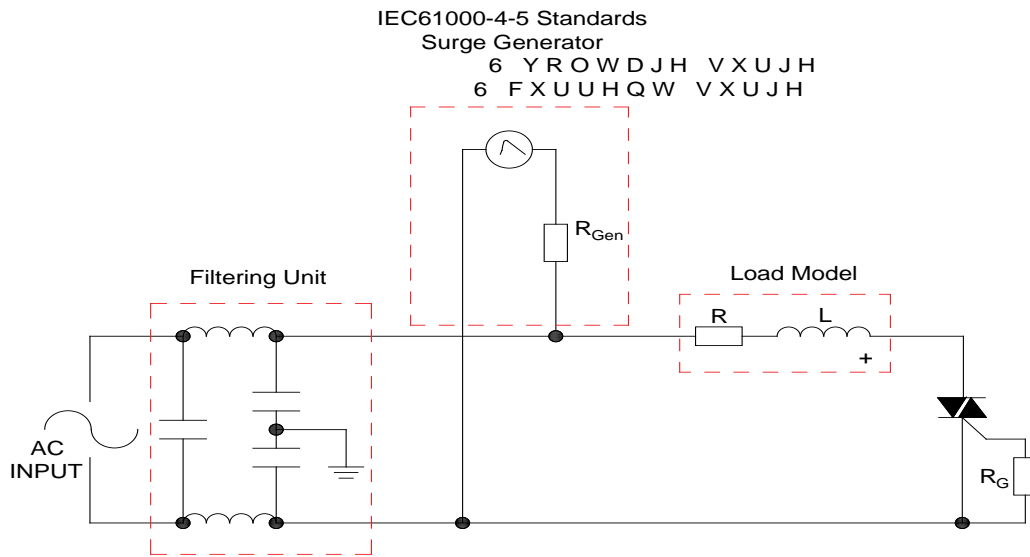


FIG.2: RMS on-state current versus case temperature

FIG.7 ÖTest circuit for inductive and resistive loads to IEC-61000-4-5 standards



## LEAD FORMING AND SOLDERING

Refer to the application note “Assembly Instructions for Thyristors in Through-hole Package” released by JieJie Microelectronics

## ORDERING INFORMATION

Order code	Voltage $V_{DRM}/V_{RRM}$ (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
		- -			
JST16C-1200SW	1200	10	TO-220C	50	Tube

## Document Revision History

PACKAGE MECHANICAL DATA



